

BEST AVAILABLE COPY**Amendments to the Claims:**

This listing of claims will replace all prior versions and listings, of claims in the application.

Listing of Claims:

1-22. Canceled

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23. (Previously Presented) A semiconductor device comprising:
a conductor layer formed on a semiconductor substrate and applied with a ground potential;
a dielectric film formed on the conductor layer; and
a conductor line formed on the dielectric film such that a bottom face of the conductor line is opposite to a top face of the conductor layer with the dielectric film interposed therebetween,
wherein the dielectric film comprises a first dielectric portion interposed between the conductor layer and the conductor line and a second dielectric portion which is formed on a side face of the first dielectric portion and has a different dielectric constant from that of the first dielectric portion.

24. (Previously Presented) The device of claim 23, wherein the first dielectric portion comprises silicon nitride, and the second dielectric portion contains titanium.

25. (Previously Presented) The device of claim 23, wherein the dielectric constant of the second dielectric portion is larger than 10.

26. (Previously Presented) The device of claim 23, further comprising a second dielectric film formed so as to cover the conductor line.

27. (Previously Presented) The device of claim 23, further comprising an active component operable at radio frequencies on the semiconductor substrate, the active

component being electrically connected with at least one of the conductor layer and the conductor line.

28. (Canceled)

29. (Previously Presented) A semiconductor device comprising:
a conductor layer formed on a semiconductor substrate and applied with a ground potential;

a dielectric film formed on the conductor layer; and

a conductor line formed on the dielectric film such that a bottom face of the conductor line is opposite to a top face of the conductor layer with the dielectric film interposed therebetween,

FI wherein the dielectric film comprises two or more dielectric layers with mutually different dielectric constants, and

wherein at least one of the two or more dielectric layers comprises:

a first dielectric portion interposed between the conductor layer and the conductor line; and

a second dielectric portion formed on a side face of the first dielectric portion and has a different dielectric constant from that of the first dielectric portion.

30. (Canceled)

31. (Canceled)

32. (Previously Presented) A semiconductor device comprising:
a conductor layer formed on a semiconductor substrate and applied with a ground potential;

a dielectric film formed on the conductor layer;

a conductor line formed on the dielectric film such that a bottom face of the conductor line is opposite to a top face of the conductor layer with the dielectric film interposed therebetween; and a second dielectric film having a dielectric constant larger than

10 formed so as to cover the conductor line,

wherein the dielectric film comprises two or more dielectric layers with mutually different dielectric constants.

33. (Canceled)

34. (Currently Amended) A semiconductor device, comprising:

a conductor layer formed on a semiconductor substrate;

a dielectric film formed on the conductor layer; and

a conductor line formed on the dielectric film, wherein the conductor layer is not formed (in a region) directly below the conductor line but in

both sides of the region thereof, and

the dielectric film consists of two dielectric layers with mutually different dielectric constants, and

the conductor line transmits an RF signal by using the conductor layer as a ground.

boundary of region not defined in claim

35. (Previously Presented) A semiconductor device comprising:

a coplanar conductor layer which is formed over a semiconductor substrate and comprises a conductor line and two conductor layers extending along the conductor line on opposite sides of the conductor line, each with a distance from the conductor line, each of the conductor layers being applied with a ground potential; and

a dielectric film formed so as to cover the coplanar conductor layer,

wherein the dielectric film has a dielectric constant larger than 10.

36. (Previously Presented) The device of claim 35, further comprising a second dielectric film which is formed between the semiconductor substrate and the coplanar conductor layer and has a dielectric constant larger than 10.

37. (Previously Presented) device of claim 35, further comprising an active component operable at radio frequencies on the semiconductor substrate, the active component being electrically connected to the coplanar conductor layer.

38. (Previously Presented) A semiconductor device comprising:
a first dielectric film formed on a semiconductor substrate;
a coplanar conductor layer formed on the first dielectric film, the coplanar conductor layer comprising a conductor line on the first dielectric film, and two conductor layers extending along the conductor line on opposite sides of the conductor line, each with a distance from the conductor line, each of the conductor layers being applied with a ground potential; and
a second dielectric film formed so as to cover the coplanar conductor layer, wherein at least one of the first and second dielectric films contains titanium.
- FI 39. (Previously Presented) The device of claim 38, wherein the first dielectric film comprises two or more dielectric layers with mutually different dielectric constants.
40. (Previously Presented) The device of claim 38, further comprising an active component operable at radio frequencies on the semiconductor substrate, the active component being electrically connected to the coplanar conductor layer.
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